Abstracts

23-GHz Band GaAs MESFET Reflection-Type Amplifier

H. Tohyama and H. Mizuno. "23-GHz Band GaAs MESFET Reflection-Type Amplifier." 1979 Transactions on Microwave Theory and Techniques 27.5 (May 1979 [T-MTT] (Special Issue on Solid-State Microwave/Millimeter-Wave Power Generation, Amplification, and Control)): 408-415.

A new method is presented for applying a packaged GaAS MESFET to an amplifier in the frequency region above 20 GHz, using package resonance as a positive feedback element and operating GaAs MESFET as a negative resistance two-terminal device in a reflection-type amplifier. Experimentally, a 6-dB noise figure in the 23-GHz band and a 8-dB noise figure in the 27-GHz band have been achieved.

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